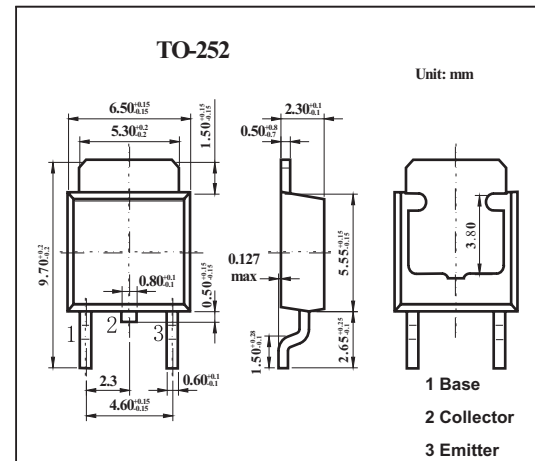


Silicon NPN Triple Diffused Type

2SC5356

■ Features

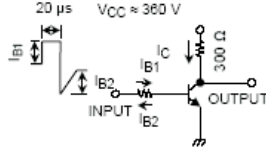
- Excellent switching times: $t_r = 0.5 \mu\text{s}$ (max) ($I_c = 1.2 \text{ A}$)
- High collectors breakdown voltage: $V_{CE0} = 800 \text{ V}$
- High DC current gain: $h_{FE} = 15$ (min) ($I_c = 0.15 \text{ A}$)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	900	V
Collector-emitter voltage	V_{CEO}	800	V
Emitter-base voltage	V_{EBO}	7	V
Collector current (DC)	I_c	3	A
Collector current (Pulse)	I_{CP}	5	
Base current	I_B	1	A
Collector power dissipation	P_c	$T_a = 25^\circ\text{C}$	1.5
		$T_c = 25^\circ\text{C}$	25
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Collector cut-off current	I _{CBO}	V _{CB} = 720 V, I _E = 0			100	μA	
Emitter cut-off current	I _{EBO}	V _{EB} = 7 V, I _C = 0			10	μA	
Collector-base breakdown voltage	V _{(BR) CBO}	I _C = 1 mA, I _E = 0	900			V	
Collector-emitter breakdown voltage	V _{(BR) CEO}	I _C = 10 mA, I _B = 0	800			V	
DC current gain	h _{FE}	V _{CE} = 5 V, I _C = 1 mA	10				
		V _{CE} = 5 V, I _C = 0.15 A	15				
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 1.2 A, I _B = 0.24 A			1.0	V	
Base-emitter saturation voltage	V _{BE (sat)}	I _C = 2 A, I _B = 0.24 A			1.3	V	
Switching time Rise time	t _r	 <p>I_{B1} = 0.24 A, I_{B2} = -0.48 A DUTY CYCLE ≤ 1%</p>			0.7	μs	
Switching time Storage time	t _{stg}						4.0
Switching time Fall time	t _f						0.5

■ Marking

Marking	C5356
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